



The products are transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

High isolation 3750 VRMS

Operating temperature range -55°C to 125°C

RoHS & REACH Compliance

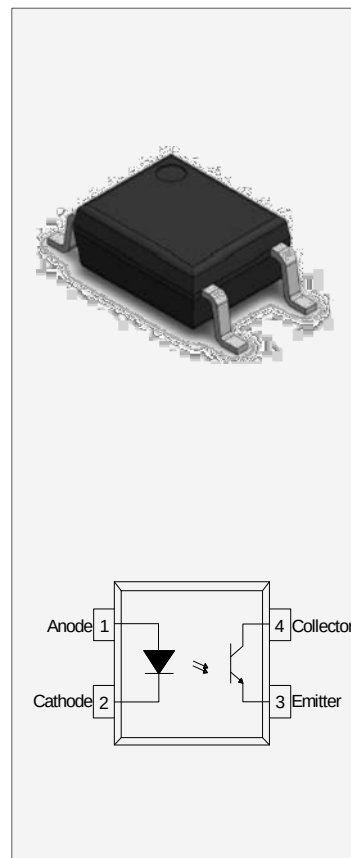
HBM: H3A; MM: M4; CDM:C3

CQC approved

VDE approved

UL approved

AECQ101 approved



(Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	7	V
	Collector Current	I_C	50	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	225	mW
Isolation Voltage		V_{iso}	3750	Vrms
Operating Temperature		T_{opr}	-55~+125	
Junction Temperature		T_j	135	

Storage Temperature	T _{stg}	-55~+125	
Soldering Temperature	T _{sol}	260	

: μ

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(Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V _F	I _F =10mA	-	1.2	1.5	V
	Reverse Current	I _R	V _R =6V	-	-	1	μA
	Terminal Capacitance	C _t	V=0, f=1MHz	-	10	-	pF
Output	Collector-Emitter dark current	I _{CEO}	V _{CE} =20V, I _F =0	-	-	100	nA
	Collector-Emitter breakdown voltage	BV _{CEO}	I _C =0.1mA I _F =0	80	-	-	V
	Emitter-Collector breakdown voltage	BV _{ECO}	I _E =0.1mA I _F =0	7	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	I _F =5mA V _{CE} =5V	80	-	600	%
	Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _F =20mA I _C =1mA	-	0.06	0.2	V
	Isolation resistance	R _{IO}	DC500V 40~60%R.H.	10 ¹²	10 ¹⁴	-	Ω
	Floating Capacitance	C _{IO}	V=0, f=1MHz	-	0.4	1	pF
	Cut-off Frequency	f _c	V _{CE} =5V, I _C =2mA R _L =100Ω, -3dB	-	80	-	kHz
	Rise Time	t _r	V _{CE} =2V, I _C =2mA R _L =100Ω	-	3	18	μs
	Fall Time	t _f		-	4	18	μs
	Response Time	t _{on}		-	6	25	μs
		t _{off}		-	5	25	μs

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Grade Sign	Min. (%)	Max. (%)

J	OC	T	357	B	h	-M4	/
JieJie Microelectronics Co., Ltd.	Opto Coupler	Transistor	Marketization Model	CTR Rank:A/B/C/D/None	h: Automotive grade	SOP4	None:T1 R:T2

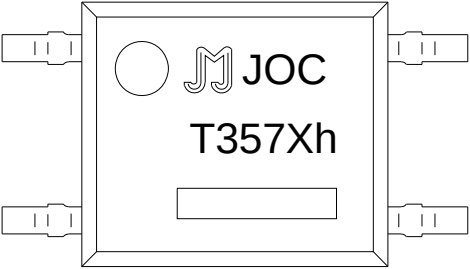
	Production Information Code
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FIG.1: Max. Allowable LED Forward Current vs. Ambient Temperature

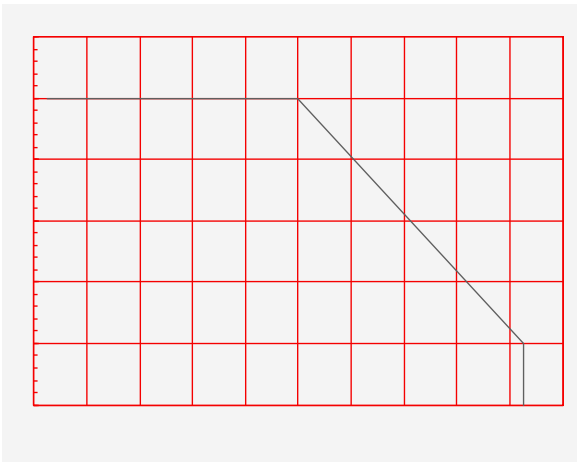


FIG.2: Collector Power Dissipation vs. Ambient Temperature

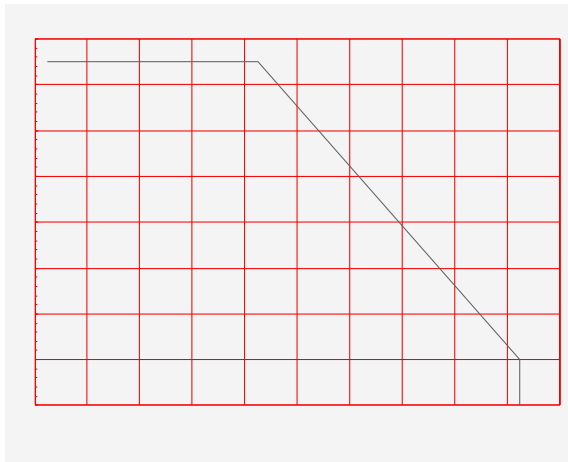


FIG.3: Forward Current vs. Forward Voltage

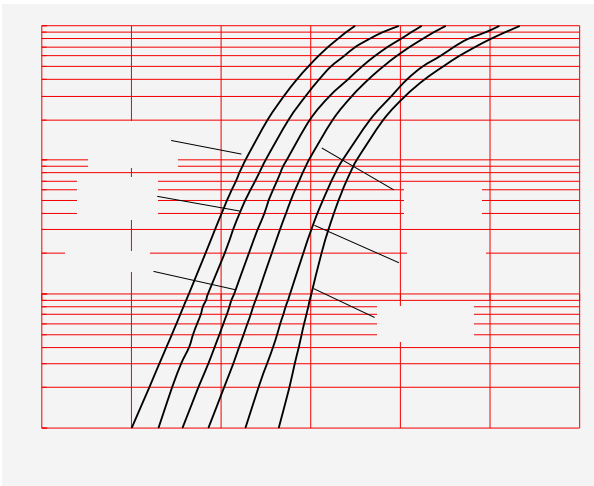


FIG.4: Normalized Collector Dark Current vs. Ambient Temperature

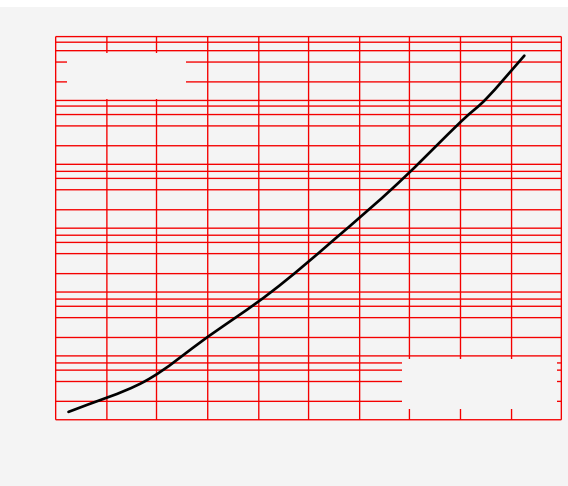


FIG.5: Collector Current vs. Collector-emitter Voltage

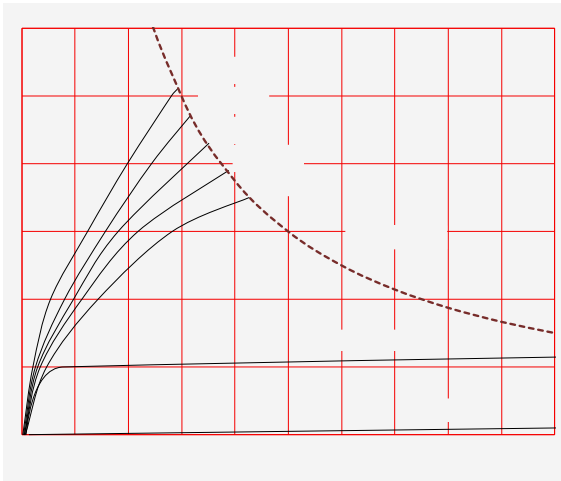


FIG.6: Normalized Current Transfer Ratio vs. Forward Current

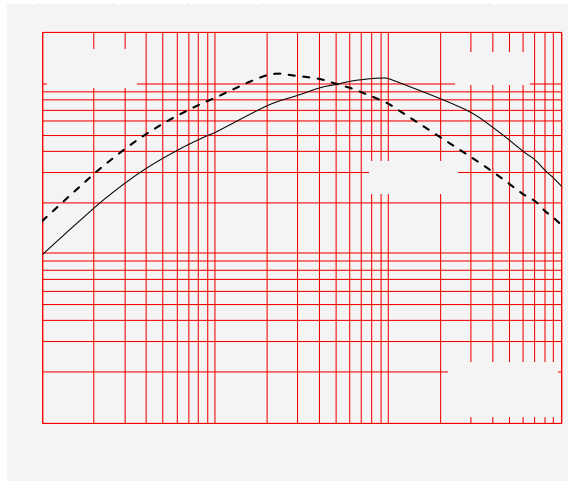


FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

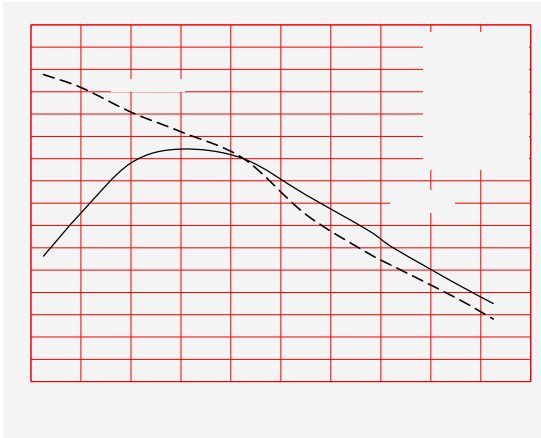


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

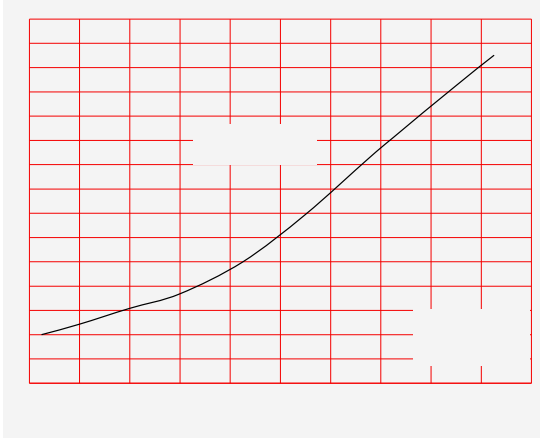


FIG.9: Response Time vs. Load Resistance

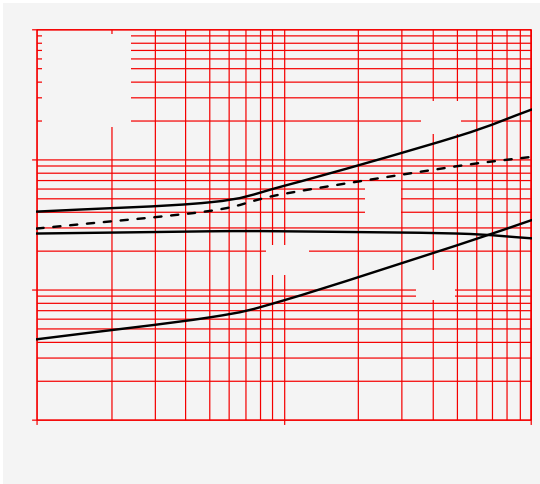


FIG.10: Frequency Response

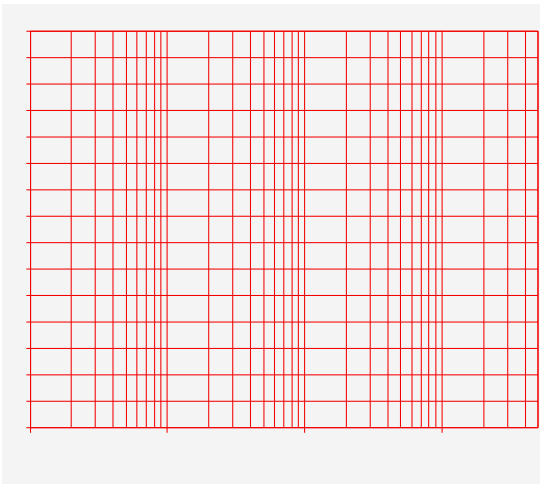


FIG.11: Test Circuits of Response Time

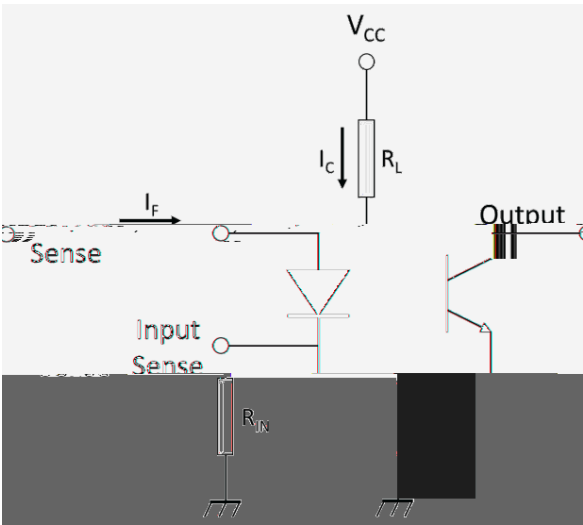


FIG.12: Curves of Response Time

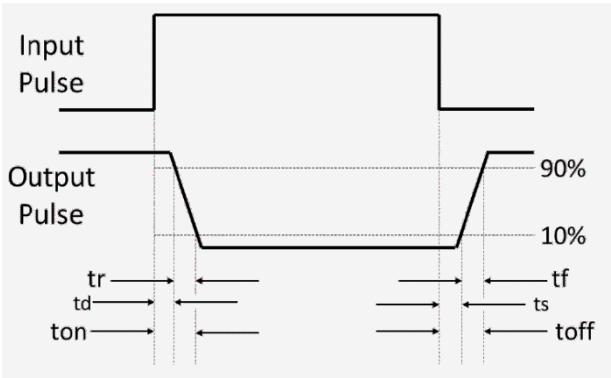
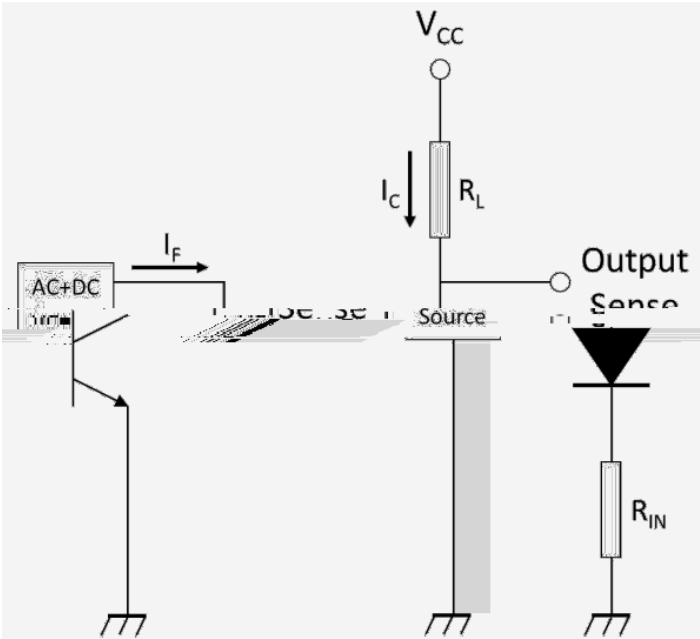
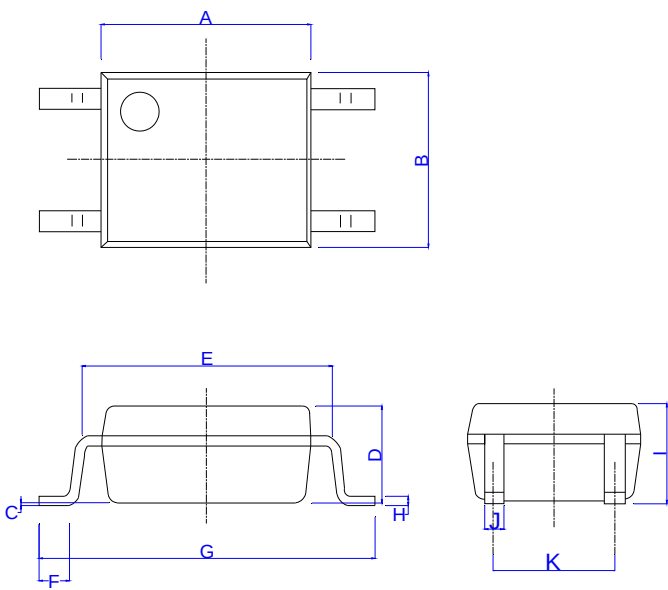
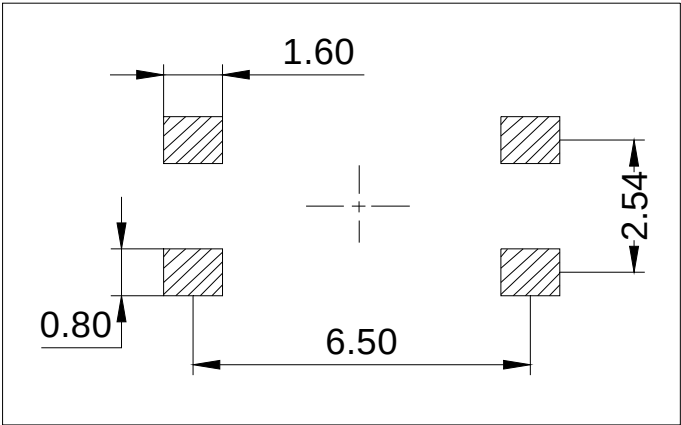


FIG.13: Test Circuits of Frequency Response

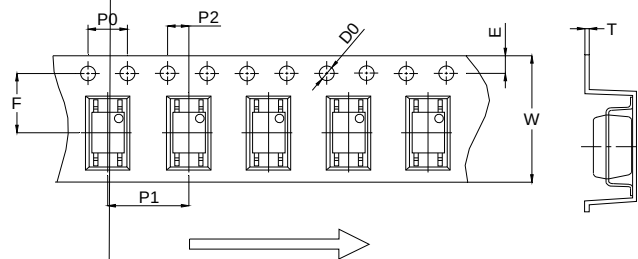




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	3.60		4.20	0.142		0.165
C	0.00		0.20	0.000		0.008
D	1.90		2.30	0.075		0.091
E	5.00		5.60	0.197		0.220
F	0.34		0.94	0.013		0.037
G	6.70		7.30	0.264		0.287
H	0.10		0.30	0.004		0.012
I	2.00		2.40	0.079		0.094
J	0.25		0.55	0.010		0.022
K	2.29		2.79	0.090		0.110

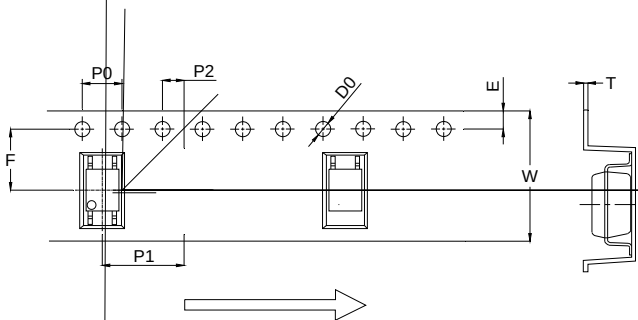


Option None

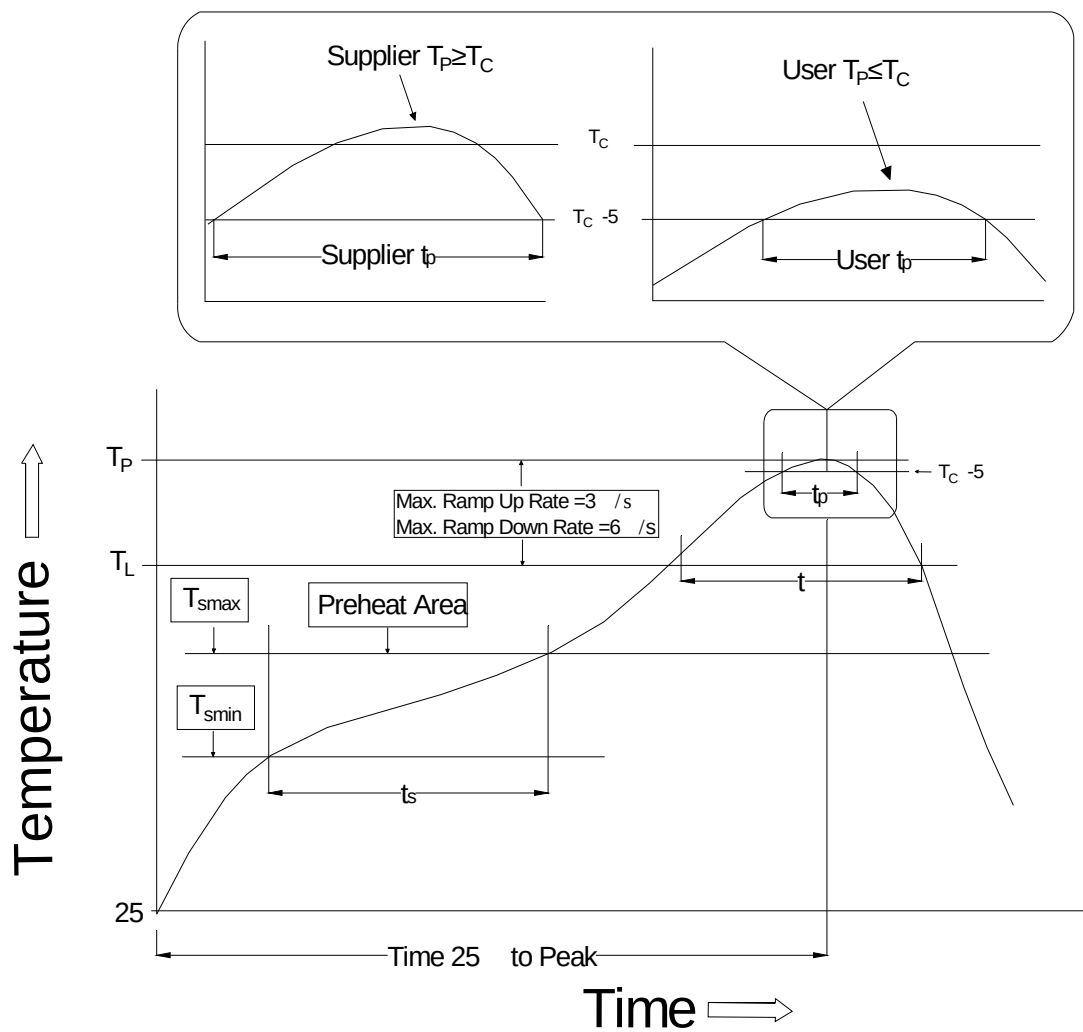


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	4.40	4.50	4.60	0.173	0.177	0.181
T	0.25	0.30	0.35	0.010	0.012	0.014
W	11.90	12.00	12.30	0.469	0.472	0.484

Option R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0						
P0						
P1						
P2						
E						
F						
T						
W						



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	100	150
Temperature Max. (T_{smax})	150	200
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t_L to T_P)	3 °C/second max.	3 °C/second max.
Liquidus Temperature (T_L)	183	217
Time (t_L) Maintained Above (T_L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time (t_P) within 5 °C of 260	10 seconds	10 seconds
Ramp-down Rate (T_P to T_L)	3-6 °C/second	3-6 °C/second
Time 25 °C to Peak Temperature	6 minutes max.	8 minutes max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;
Recommend storage humidity: <60%;
MSL level: MSL 1

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